

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	J/m\$5 with ("silicon nitride" or sin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 10:48
L2	2	("SiOC" near2 insulat\$3) and "flip chip"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:48
L3	5832	"insulating film" near3 ("silicon nitride" or polyimide or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:49
L4	1693	"insulating film" near ("silicon nitride" or polyimide or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:49
L5	1475	"insulating film" adj ("silicon nitride" or polyimide or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 12:50
L6	19	"insulating film" adj (benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:30
L7	301	"silicon dioxide" near organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:32
L8	119	"passivation layer" with electrode with (polyimide or bcb or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:35

L9	18	"passivation" with bump with (polyimide or bcb or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:47
L10	2	("6306680").PN. OR ("6617696").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/14 13:38
L11	123	"passivation" with bump with (polyimide or bcb or benzocyclobutene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 13:47
S1	6	((("6311888") or ("5985043") or ("6228680")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/10 14:54
S2	1017	(257/783).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:23
S3	2464	(257/778).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:24
S4	12	("5691103" "5736681" "5865934" "5874780" "5971253" "6202915" "6204089" "6243946").PN. OR ("6311888").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/13 10:05
S5	12	("20010051392" "5136365" "5925930" "6121689" "6234379" "6238948" "6265776" "6316286" "6335571" "6337265" "6518677" "6639321").PN. OR ("6815831").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/13 10:29

S6	19	(US-20030173683-\$ or US-20030001283-\$ or US-20020171156-\$ or US-20040253803-\$ or US-20040222522-\$).did. or (US-6774497-\$ or US-6774493-\$ or US-6426566-\$ or US-6365840-\$ or US-6815831-\$ or US-6311888-\$ or US-5874780-\$ or US-6639321-\$ or US-6518677-\$ or US-6335571-\$ or US-5925930-\$ or US-5691103-\$ or US-6204089-\$ or US-6228680-\$). did.	US-PGPUB; USPAT	OR	ON	2005/06/13 13:01
S7	186	third near (resin or underfill) near layer	US-PGPUB; USPAT	OR	ON	2005/06/13 13:02
S8	110	third adj (resin or underfill) adj layer	US-PGPUB; USPAT	OR	ON	2005/06/13 13:30
S9	1139	"flip chip" and passivation and (insulat\$3 adj (film or layer))	US-PGPUB; USPAT	OR	ON	2005/06/13 13:31
S10	231	"flip chip" and passivation and (insulat\$3 adj (film or layer)) and resin and reflow	US-PGPUB; USPAT	OR	ON	2005/06/13 15:07
S11	2	("6121689").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 16:24
S12	0	("("adhesionstrength"oradhesiveness)with("siliconnitride"orsin")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 16:26
S13	167	("adhesion strength" or adhesiveness) with ("silicon nitride" or sin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 16:32
S14	1	J/m with ("silicon nitride" or sin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 10:06